

**MMBTA64****PNP EPITAXIAL SILICON TRANSISTOR**

T-29-29

**DARLINGTON TRANSISTOR****ABSOLUTE MAXIMUM RATINGS (T<sub>a</sub>=25°C)**

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V <sub>CB0</sub>	30	V
Collector-Emitter Voltage	V <sub>CES</sub>	30	V
Emitter-Base Voltage	V <sub>EB0</sub>	10	V
Collector Current	I <sub>C</sub>	500	mA
Collector Dissipation	P <sub>C</sub>	350	mW
Storage Temperature	T <sub>stg</sub>	150	°C

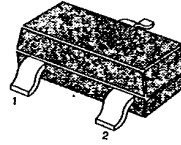
• Refer to MMBTA63 for graphs

**ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C)**

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector-Emitter Breakdown Voltage	BV <sub>CES</sub>	I <sub>C</sub> =100μA, I <sub>B</sub> =0	30		V
Collector Cutoff Current	I <sub>CB0</sub>	V <sub>CB</sub> =30V, I <sub>E</sub> =0		100	nA
Emitter Cutoff Current	I <sub>EB0</sub>	V <sub>BE</sub> =10V, I <sub>C</sub> =0		100	nA
*DC Current Gain	h <sub>FE</sub>	V <sub>CE</sub> =5V, I <sub>C</sub> =10mA V <sub>CE</sub> =5V, I <sub>C</sub> =100mA	10,000 20,000		
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =100mA, I <sub>B</sub> =0.1mA		1.5	V
Base-Emitter On Voltage	V <sub>BE(on)</sub>	I <sub>C</sub> =100mA, V <sub>CE</sub> =5V		2	V
Current Gain-Bandwidth Product	f <sub>r</sub>	I <sub>C</sub> =10mA, V <sub>CL</sub> =50V f=100MHz	125		MHz

\*Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%

SOT-23



1. Base 2. Emitter 3. Collector

Marking

